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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







Preferred Devices

### **Thyristor Surge Protectors**

### **High Voltage Bidirectional TSPD**

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover–triggered crowbar protectors. Turn–off occurs when the surge current falls below the holding current value.

Secondary protection applications for electronic telecom equipment at customer premises.

#### **Features**

- High Surge Current Capability: 80 Amps 10 x 1000 μsec, for Controlled Temperature Environments
- The MMT08B260T3 is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68.
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non–Semiconductor Devices
- Fail-Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation
- Surface Mount Technology (SMT)
- N Indicates UL Registered File #E210057
- Pb-Free Package is Available

#### MAXIMUM RATINGS (T.I = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Off-State Voltage - Maximum	$V_{DM}$	±200	V
Maximum Pulse Surge Short Circuit Current Non-Repetitive Double Exponential Decay Waveform (-25°C Initial Temperature) (Notes 1 & 2) 2 x 10 µsec 8 x 20 µsec 10 x 160 µsec 10 x 360 µsec 10 x 560 µsec 10 x 700 µsec 10 x 1000 µsec	IPPS2 IPPS3 IPPS4 IPPS5 IPPS6	±250 ±250 ±150 ±150 ±100 ±100 ±80	A(pk)
Non-Repetitive Peak On-State Current 60 Hz Full Sign Wave	I <sub>TSM</sub>	32	A(pk)
	di/dt	±300	A/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Allow cooling before testing second polarity.
- Measured under pulse conditions to reduce heating.



### ON Semiconductor®

http://onsemi.com

# BIDIRECTIONAL TSPD (%) 80 AMP SURGE, 260 VOLTS





SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C

### MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
RPCG = Device Code
Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMT08B260T3	SMB	2500 Tape & Reel
MMT08B260T3G	SMB (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T <sub>J1</sub>	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T <sub>J2</sub>	+175	°C
Instantaneous Peak Power Dissipation (I <sub>pk</sub> = 50 A, 10x1000 μsec @ 25°C)	P <sub>PK</sub>	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

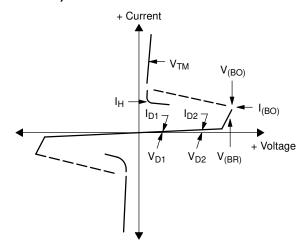
# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted) Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

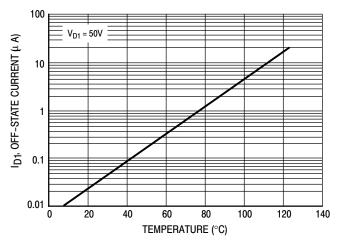
Characteristics	Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both polarities) $ (dv/dt = 100 \text{ V/}\mu\text{s}, \text{ I}_{SC} = 1.0 \text{ A}, \text{ Vdc} = 1000 \text{ V}) \\ (+65^{\circ}\text{C}) $	V <sub>(BO)</sub>		- -	320 340	V
Breakover Voltage (Both polarities) $ \begin{array}{l} (f=60~Hz,~I_{SC}=1.0~A(rms),~V_{OC}=1000~V(rms),\\ R_I=1.0~k\Omega,~t=0.5~cycle)~(Note~3)\\ (+65^{\circ}C) \end{array} $	V <sub>(BO)</sub>	_ _	_ _	320 340	V
Breakover Voltage Temperature Coefficient	$dV_{(BO)}/dT_{J}$	-	0.08	-	%/°C
Breakdown Voltage (I <sub>(BR)</sub> = 1.0 mA) Both polarities	V <sub>(BR)</sub>	-	260	-	V
Off State Current ( $V_{D1} = 50 \text{ V}$ ) Both polarities ( $V_{D2} = V_{DM}$ ) Both polarities	I <sub>D1</sub> I <sub>D2</sub>	- -	_	2.0 5.0	μΑ
On–State Voltage ( $I_T$ = 1.0 A) (PW $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 2%) (Note 3)	V <sub>T</sub>	-	1.53	3.0	V
Breakover Current (f = 60 Hz, $V_{DM}$ = 1000 V(rms), $R_S$ = 1.0 k $\Omega$ ) Both polarities	I <sub>BO</sub>	-	230	-	mA
Holding Current (Both polarities) (Note 3) $V_S = 500$ Volts; $I_T$ (Initiating Current) = $\pm 1.0$ Amp	I <sub>H</sub>	150 -	300 -	- -	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V <sub>D</sub> = Rated V <sub>BR</sub> , T <sub>J</sub> = 25°C)	dv/dt	2000	-	-	V/μs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal) (f = 1.0 MHz, 2.0 Vdc, 1.0 mV rms Signal)	Co	_ _	25 50	30 55	pF

<sup>3.</sup> Measured under pulse conditions to reduce heating.

# Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter	
I <sub>D1</sub> , I <sub>D2</sub>	Off State Leakage Current	
$V_{D1}, V_{D2}$	Off State Blocking Voltage	
V <sub>BR</sub>	Breakdown Voltage	
V <sub>BO</sub>	Breakover Voltage	
I <sub>BO</sub>	Breakover Current	
I <sub>H</sub>	Holding Current	
V <sub>TM</sub>	On State Voltage	

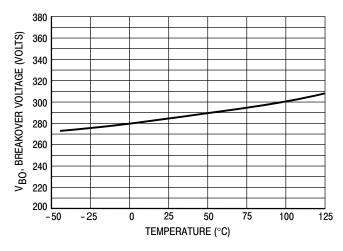




340 V<sub>BR</sub>, BREAKDOWN VOLTAGE (VOLTS) 320 300 280 260 240 220 200 180 160 - 50 -25 50 75 100 125 TEMPERATURE (°C)

Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature



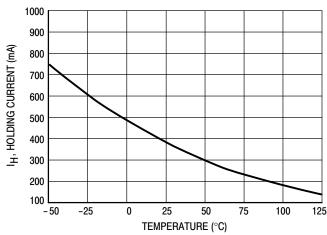
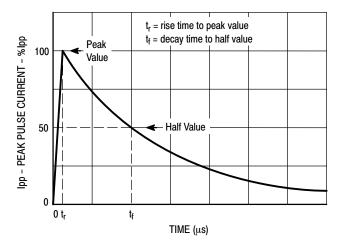


Figure 3. Breakover Voltage versus Temperature

Figure 4. Holding Current versus Temperature



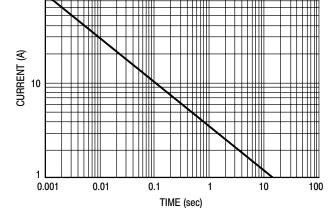
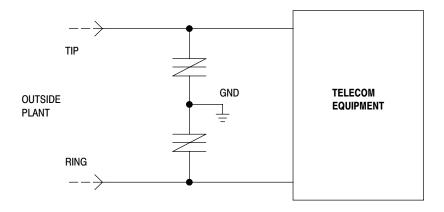
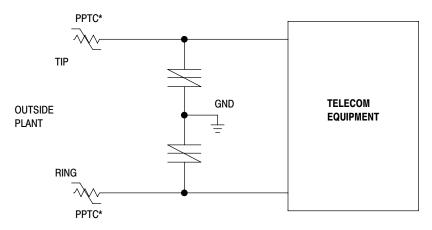


Figure 5. Exponential Decay Pulse Waveform

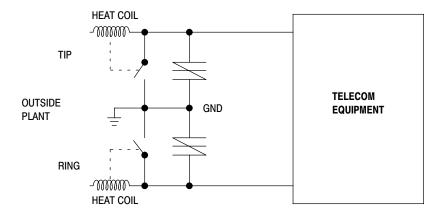
Figure 6. Peak Surge On-State Current versus Surge Current Duration, Sinusoidal Waveform

100



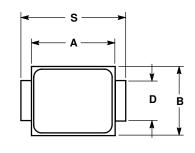


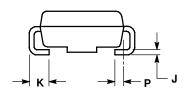
\*Polymeric PTC (positive temperature coefficient) overcurrent protection device

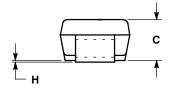


### PACKAGE DIMENSIONS

### **SMB** CASE 403C-01 ISSUE A



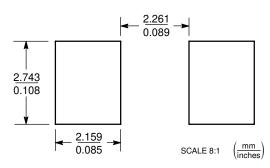




- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
Р	0.020 REF		0.51	REF
S	0.205	0.220	5.21	5.59

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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